Microsemi
POWER PRODUCTS GROUP

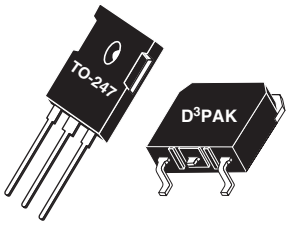
APT77N60BC6
APT77N60SC6

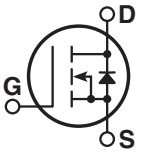
600V 77A 0.041Ω

COOLMOS
Power Semiconductors

Super Junction MOSFET

- Ultra Low $R_{DS(ON)}$
- Low Miller Capacitance
- Ultra Low Gate Charge, Q_g
- Avalanche Energy Rated
- Extreme $^{dv}/_{dt}$ Rated
- Popular TO-247 or Surface Mount D^3 package.





MAXIMUM RATINGS

All Ratings per die: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT77N60B_SC6	UNIT
V_{DSS}	Drain-Source Voltage	600	Volts
I_D	Continuous Drain Current @ T_C = 25°C	77	Amps
	Continuous Drain Current @ T_C = 100°C	49	
I_{DM}	Pulsed Drain Current [1]	272	
V_{GS}	Gate-Source Voltage Continuous	±20	Volts
P_D	Total Power Dissipation @ T_C = 25°C	481	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	- 55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current [2]	13.4	Amps
E_{AR}	Repetitive Avalanche Energy [2] (Id =13.4A, Vdd = 50V)	2.96	mJ
E_{AS}	Single Pulse Avalanche Energy (Id = 13.4A, Vdd = 50V)	1954	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{(DSS)}$	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250µA)	600			Volts
$R_{DS(on)}$	Drain-Source On-State Resistance [3] (V_{GS} = 10V, I_D = 44.4A)		.037	.041	Ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = V_{DSS}, V_{GS} = 0V, T_C = 25°C)			25	µA
	Zero Gate Voltage Drain Current (V_{DS} = V_{DSS}, V_{GS} = 0V, T_C = 150°C)			250	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±20V, V_{DS} = 0V)			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 2.96mA)	2.5	3	3.6	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trademark of Infineon Technologies AG."

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		13600		pF
C_{oss}	Output Capacitance			4400		
C_{rss}	Reverse Transfer Capacitance			290		
Q_g	Total Gate Charge [4]	V_{GS} = 10V V_{DD} = 400V I_D = 77A @ 25°C		260		nC
Q_{gs}	Gate-Source Charge			38		
Q_{gd}	Gate-Drain ("Miller") Charge			144		
$t_{d(on)}$	Turn-on Delay Time	**INDUCTIVE SWITCHING** V_{GS} = 10V V_{DD} = 380V I_D = 77A @ 25°C R_G = 5.0Ω		18		ns
t_r	Rise Time			27		
$t_{d(off)}$	Turn-off Delay Time			110	165	
t_f	Fall Time			8	12	
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 25°C** V_{DD} = 400V, V_{GS} = 15V I_D = 77A, R_G = 5Ω		1670		µJ
E_{off}	Turn-off Switching Energy			2880		
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 125°C** V_{DD} = 400V, V_{GS} = 15V I_D = 77A, R_G = 5Ω		2300		
E_{off}	Turn-off Switching Energy			3100		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)				77	Amps
I_{SM}	Pulsed Source Current [1] (Body Diode)				231	
V_{SD}	Diode Forward Voltage [3] (V_{GS} = 0V, I_S = -77A)			1	1.2	Volts
$^{dv}/_{dt}$	Peak Diode Recovery $^{dv}/_{dt}$ [6]				15	V/ns
t_{rr}	Reverse Recovery Time (I_S = -77A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		950		ns
Q_{rr}	Reverse Recovery Charge (I_S = -77A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		32		µC
I_{RRM}	Peak Recovery Current (I_S = -77A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		60		Amps

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.26	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

1 Repetitive Rating: Pulse width limited by maximum junction temperature

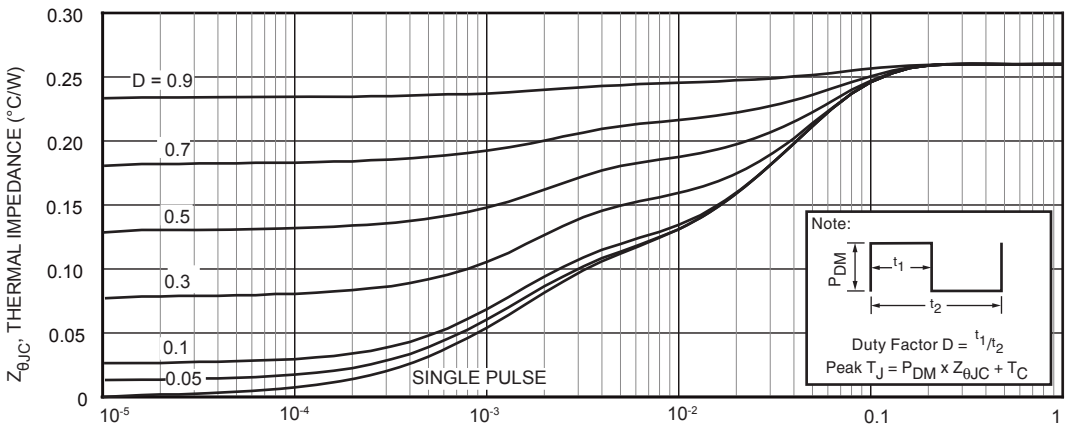
2 Repetitive avalanche causes additional power losses that can be calculated as ***$P_{AV} = E_{AR} * f$. Pulse width tp limited by Tj max.***

3 Pulse Test: Pulse width < 380 µs, Duty Cycle < 2%

4 See MIL-STD-750 Method 3471

5 Eon includes diode reverse recovery.

6 Maximum 125°C diode commutation speed = di/dt 600A/µs



RECTANGULAR PULSE DURATION (SECONDS)

Figure 1, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

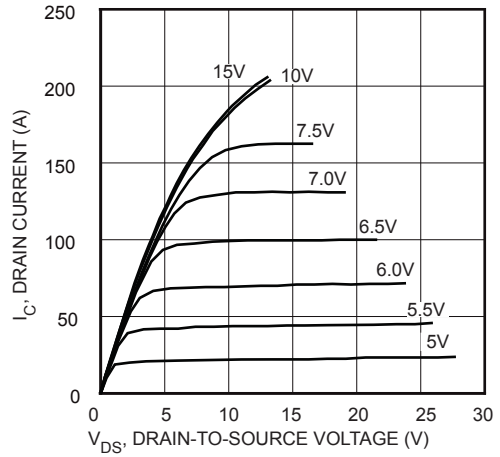


FIGURE 2, Low Voltage Output Characteristics

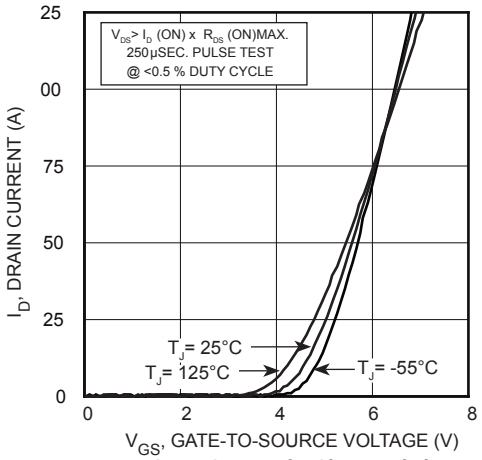


FIGURE 3, Transfer Characteristics

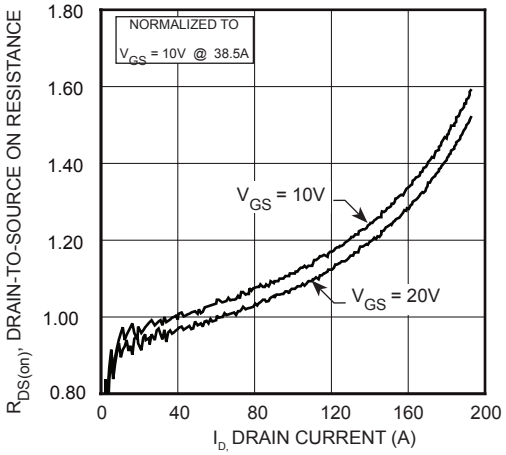


FIGURE 4, R_{DS}(ON) vs Drain Current

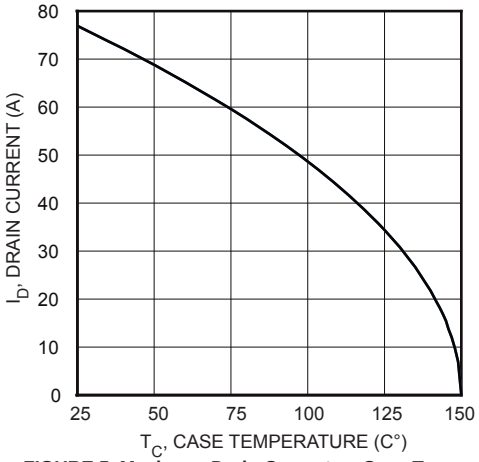


FIGURE 5, Maximum Drain Current vs Case Temperature

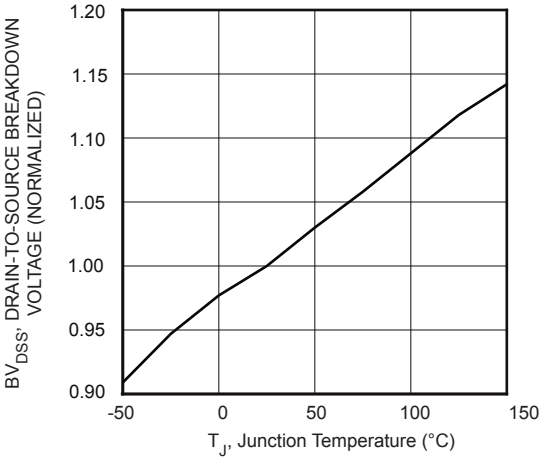


FIGURE 6, Breakdown Voltage vs Temperature

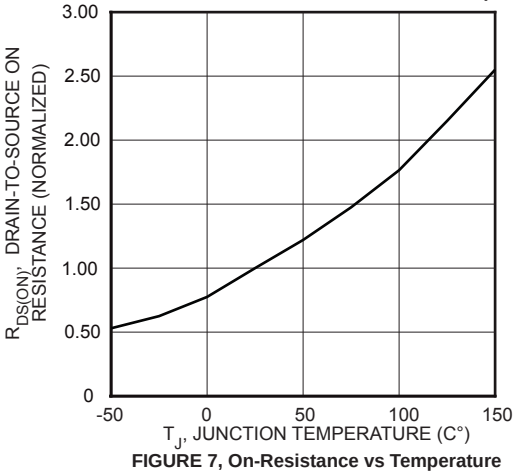


FIGURE 7, On-Resistance vs Temperature

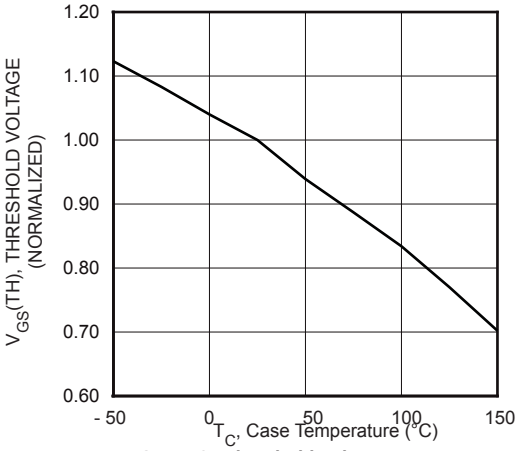


FIGURE 8, Threshold Voltage vs Temperature

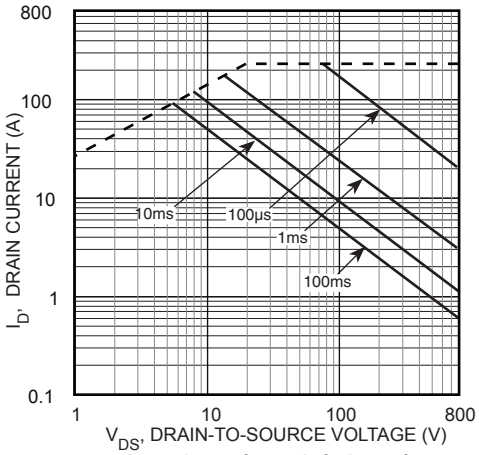


FIGURE 9, Maximum Safe Operating Area

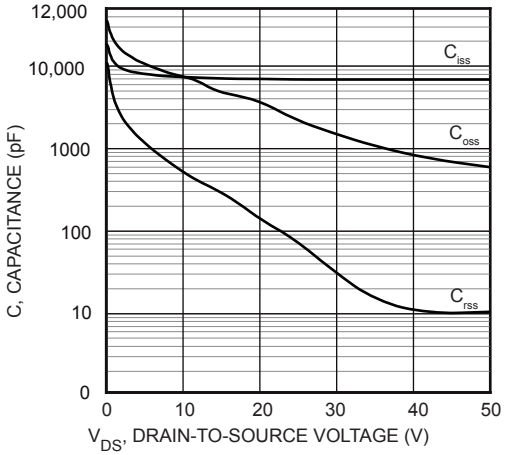


FIGURE 10, Capacitance vs Drain-To-Source Voltage

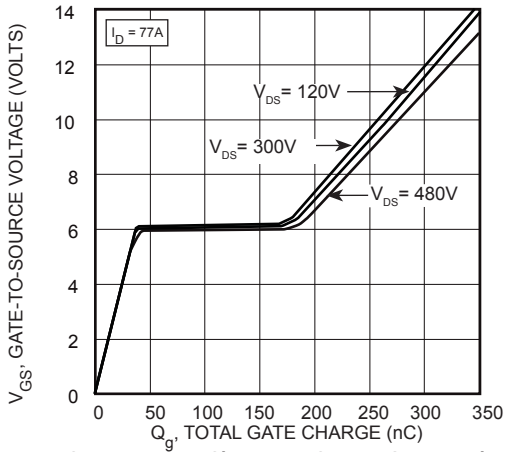


FIGURE 11, Gate Charges vs Gate-To-Source Voltage

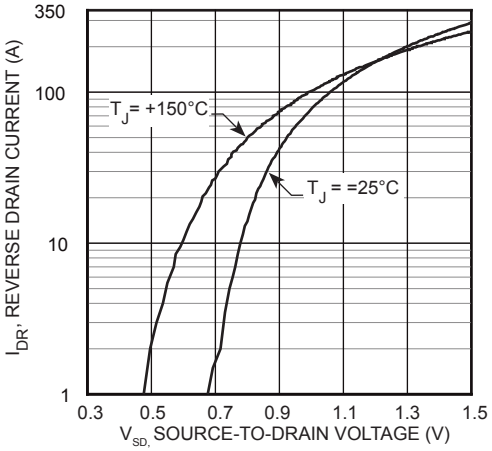


FIGURE 12, Source-Drain Diode Forward Voltage

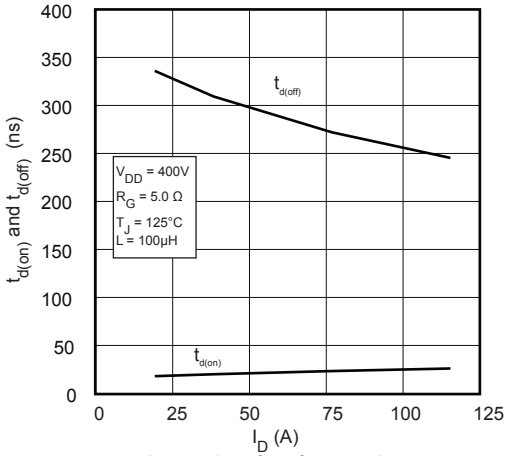


FIGURE 13, Delay Times vs Current

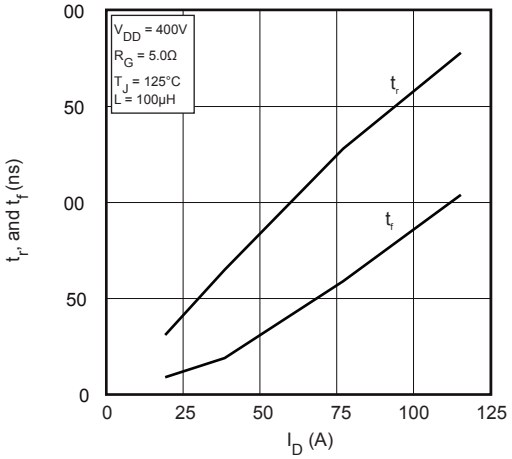


FIGURE 14 , Rise and Fall Times vs Current

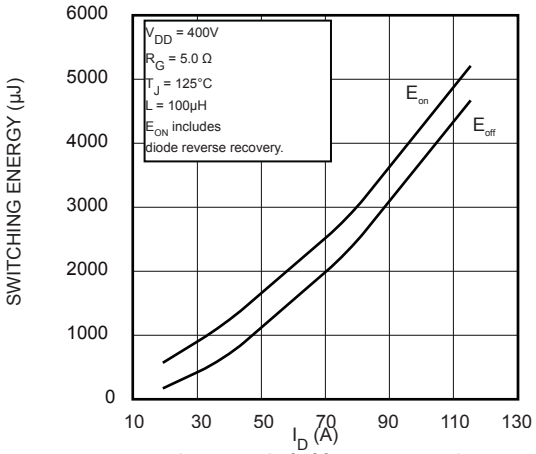


FIGURE 15, Switching Energy vs Current

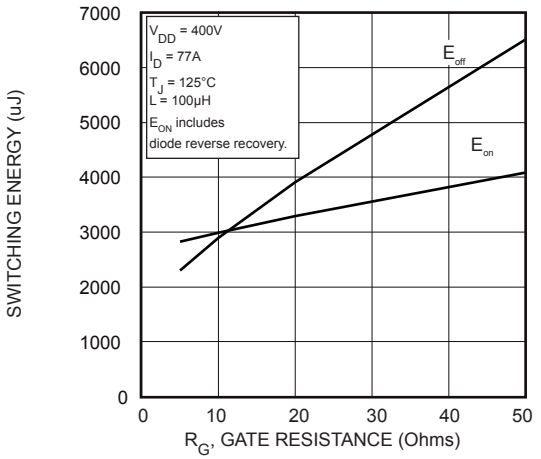


FIGURE 16, Switching Energy vs Gate Resistance

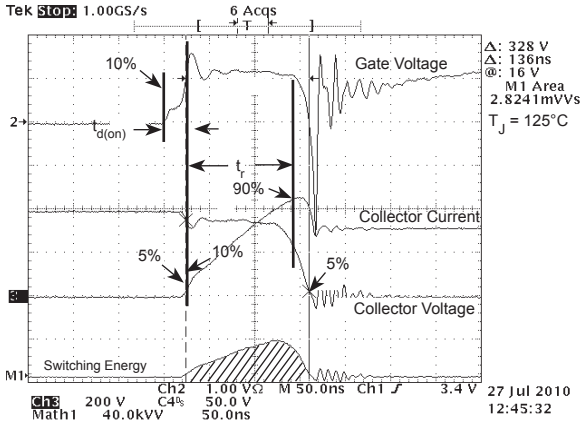


Figure 17, Turn-on Switching Waveforms and Definitions

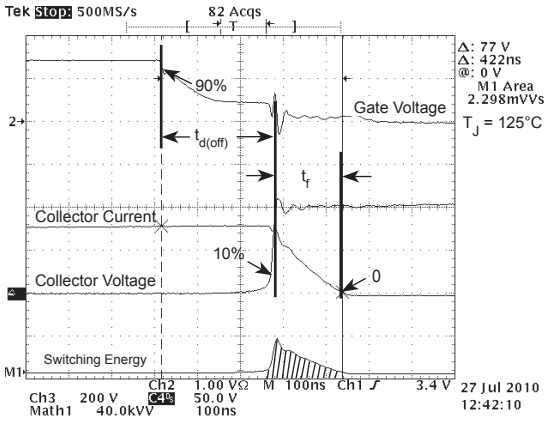


Figure 18, Turn-off Switching Waveforms and Definitions

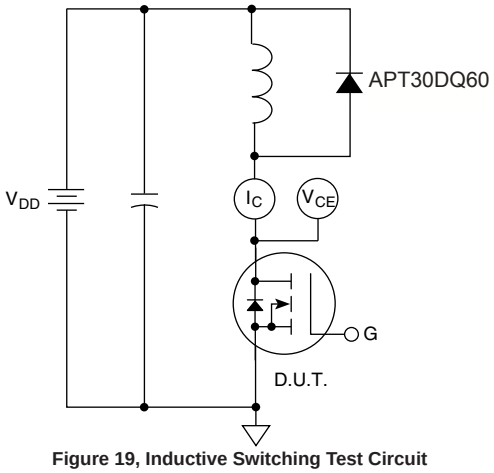
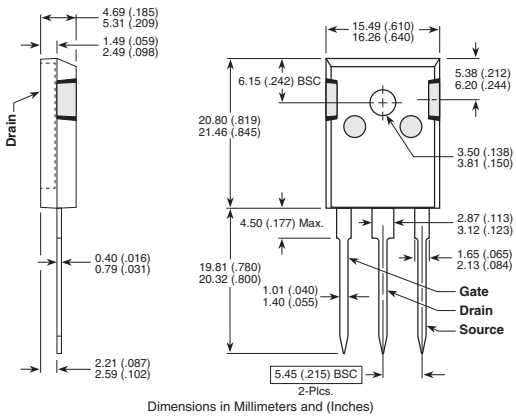


Figure 19, Inductive Switching Test Circuit

TO-247 Package Outline

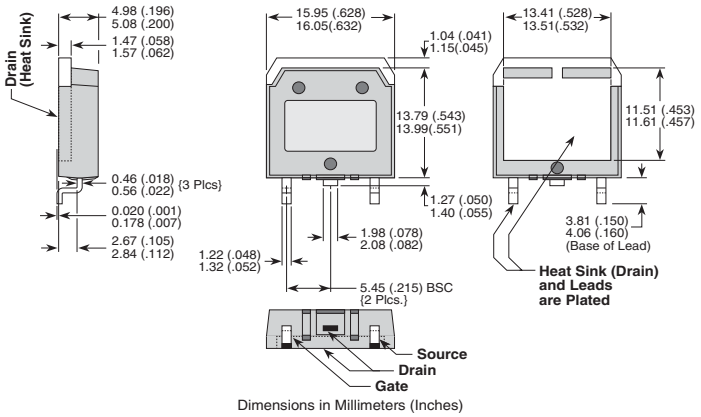
e1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

D³PAK Package Outline

e3 100% Sn



Dimensions in Millimeters (Inches)

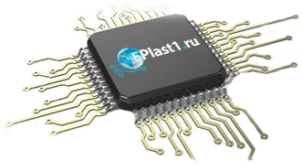
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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